

## SEMITOP<sup>®</sup> 4 Press-Fit

## **IGBT** module

### Engineering Sample SK150GAH12T4Tp

#### Target Data

#### Features

- One screw mounting module
- Solder free mounting with Press-Fit
- terminals

  Fully compatible with other SEMITOP<sup>®</sup>
  2 and 3 Press-Fit
- Improved thermal performances by aluminum oxide substrate
- Trench4 IGBT technology
- CAL4F diode technology
- Integrated PTC temperature sensor
- UL recognized, file no. E 63 532

#### **Typical Applications\***

- Switching SR Drives
- Inverter
- Switched mode power supplies

• UPS

## Absolute Maximum Ratings

Symbol	Conditions		Values	Unit			
IGBT 1							
V <sub>CES</sub>	T <sub>j</sub> = 25 °C		1200	V			
lc	T = 175 °C	T <sub>s</sub> = 25 °C	167	А			
	- 1j - 175 C	T <sub>s</sub> = 70 °C	135	А			
I <sub>Cnom</sub>			150	А			
I <sub>CRM</sub>	I <sub>CRM</sub> = 3 x I <sub>Cnom</sub>		450	А			
V <sub>GES</sub>			-20 20	V			
t <sub>psc</sub>	$V_{CC} = 800 V$ $V_{GE} \le 15 V$ $V_{CES} \le 1200 V$	T <sub>j</sub> = 150 °C	10	μs			
Tj		<b>.</b>	-40 175	°C			

#### **Absolute Maximum Ratings**

Symbol	Conditions		Values	Unit
Diode 1				
V <sub>RRM</sub>	T <sub>j</sub> = 25 °C		1200	V
I <sub>F</sub>	T 175 °C	T <sub>s</sub> = 25 °C	33	А
	$I_j = 1/5 ^{\circ}\text{C}$	T <sub>s</sub> = 70 °C	27	А
I <sub>Fnom</sub>			16	А
I <sub>FRM</sub>	I <sub>FRM</sub> = 3 x I <sub>Fnom</sub>		48	А
I <sub>FSM</sub>	10 ms, sin 180°	°, T <sub>j</sub> = 150 °C	65	А
Tj			-40 175	°C

### Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Diode 2				
V <sub>RRM</sub>	T <sub>j</sub> = 25 °C		1200	V
l <sub>F</sub>	T 175 °C	T <sub>s</sub> = 25 °C	155	А
	$= 1_{j} = 175$ C	T <sub>s</sub> = 70 °C	123	Α
I <sub>Fnom</sub>			150	Α
I <sub>FRM</sub>	I <sub>FRM</sub> = 3 x I <sub>Fnom</sub>		450	А
I <sub>FSM</sub>	10 ms, sin 180°	°, T <sub>j</sub> = 150 °C	774	А
Tj			-40 175	°C

Absolute Maximum Ratings							
Symbol	Conditions	Values	Unit				
Module							
I <sub>t(RMS)</sub>	$T_{terminal} = 100 \ ^{\circ}C, T_{S} = 60 \ ^{\circ}C$	40	Α				
T <sub>stg</sub>		-40 125	°C				
V <sub>isol</sub>	AC, sinusoidal, 50Hz, t = 1 min	2500	V				





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Characte	eristics					
Symbol	Conditions		min.	typ.	max.	Unit
IGBT 1	•					
V <sub>CE(sat)</sub>	I <sub>C</sub> = 150 A	T <sub>j</sub> = 25 °C		1.85	2.10	V
	V <sub>GE</sub> = 15 V chiplevel	T <sub>j</sub> = 150 °C		2.25	2.45	V
V <sub>CE0</sub>	chiplevel	T <sub>j</sub> = 25 °C		0.80	0.90	V
	Chiplevel	T <sub>j</sub> = 150 °C		0.70	0.80	V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25 °C		7.0	8.0	mΩ
	chiplevel	T <sub>j</sub> = 150 °C		10	11	mΩ
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_C = 6$	mA	5	5.8	6.5	V
I <sub>CES</sub>	$V_{GE} = 0 V$	T <sub>j</sub> = 25 °C			2	mA
	V <sub>CE</sub> = 1200 V			-		mA
Cies		f = 1 MHz		8.8		nF
Coes	$V_{CE} = 25 V$ $V_{CE} = 0 V$	f = 1 MHz		0.58		nF
C <sub>res</sub>		f = 1 MHz		0.47		nF
Q <sub>G</sub>	- 8 V+ 15 V			850		nC
R <sub>Gint</sub>	T <sub>j</sub> = 25 °C			5.0		Ω
t <sub>d(on)</sub>	$V_{CC} = 600 V$	T <sub>j</sub> = 150 °C				ns
t <sub>r</sub>	$I_{\rm C} = 150 \rm{A}$	T <sub>j</sub> = 150 °C				ns
Eon	$R_{G \text{ on}} = 2 \Omega$	T <sub>j</sub> = 150 °C		10.8		mJ
t <sub>d(off)</sub>		T <sub>j</sub> = 150 °C				ns
t <sub>f</sub>		T <sub>j</sub> = 150 °C				ns
E <sub>off</sub>	V <sub>GE neg</sub> = -15 V V <sub>GE pos</sub> = 15 V	T <sub>j</sub> = 150 °C		15.6		mJ
R <sub>th(j-s)</sub>	per IGBT			0.33		K/W

Characte	ristics					
Symbol	Conditions		min.	typ.	max.	Unit
Diode 1						
V <sub>F</sub>	I <sub>F</sub> = 16 A	T <sub>j</sub> = 25 °C		2.33	2.65	V
	chiplevel	T <sub>j</sub> = 150 °C		2.35	2.68	V
V <sub>F0</sub>	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V
		T <sub>j</sub> = 150 °C		0.90	1.10	V
r <sub>F</sub>	chiployol	T <sub>j</sub> = 25 °C		64	72	mΩ
	Chipievei	T <sub>j</sub> = 150 °C		91	99	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 16 A	T <sub>j</sub> = 150 °C		-		Α
Q <sub>rr</sub>		T <sub>j</sub> = 150 °C		-		μC
Err	$v_{GE} = -15 V$ $V_{CC} = 600 V$	T <sub>j</sub> = 150 °C		0.82		mJ
R <sub>th(j-s)</sub>	per Diode			1.1		K/W





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Characteristics							
Symbol	Conditions		min.	typ.	max.	Unit	
Diode 2							
V <sub>F</sub>	I <sub>F</sub> = 150 A	T <sub>j</sub> = 25 °C		2.17	2.49	V	
	chiplevel	T <sub>j</sub> = 150 °C		2.11	2.42	V	
V <sub>F0</sub>	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V	
		T <sub>j</sub> = 150 °C		0.90	1.10	V	
r <sub>F</sub>	chiployol	T <sub>j</sub> = 25 °C		5.8	6.6	mΩ	
		T <sub>j</sub> = 150 °C		8.1	8.8	mΩ	
I <sub>RRM</sub>	I <sub>F</sub> = 150 A	T <sub>j</sub> = 150 °C				A	
Q <sub>rr</sub>	V15 V	T <sub>j</sub> = 150 °C				μC	
E <sub>rr</sub>	$V_{CC} = 600 V$	T <sub>j</sub> = 150 °C		10.3		mJ	
R <sub>th(j-s)</sub>	per Diode			0.42		K/W	

Characteristics							
Symbol	Conditions	min.	typ.	max.	Unit		
Module							
Ms	to heatsink	2.5		2.75	Nm		
w	weight		60		g		

Characteristics							
Symbol	Conditions	min.	typ.	max.	Unit		
Temperat	ure Sensor						
R <sub>100</sub>	T <sub>r</sub> =100°C (R <sub>25</sub> =1000Ω)		1670 ± 3%		Ω		
R(T)	$\begin{split} &R(T){=}1000\Omega[1{+}A(T{-}25^\circC){+}B(T{-}25^\circC)^2\\ ],A=7.635^{*}10^{\cdot3}^\circC^{\cdot1},\\ &B=1.731^{*}10^{\cdot5}^\circC^{\cdot2} \end{split}$						







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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